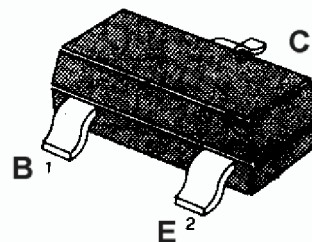


MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _c	-600	mA
Collector Power Dissipation	P _c	330	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C

SOT-23


1.Base 2 .Emitter 3 .Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	100		300		V _{CE} = -2V, I _c = -150mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -35V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -3V, I _c =0
Collector-Base Breakdown Voltage	BV _{CBO}	-40			V	I _c = -0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40			V	I _c = -1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5			V	I _E = -0.1mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.5	V	I _c = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1.3	V	I _c = -500mA, I _B = -50mA
Gain bandwidth product	f _r	200			MHz	I _c = -20mA, V _{CE} = -10V, f=100MHz
Turn on Time	t _{on}			35	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = -15mA
Turn off Time	t _{off}			255	ns	V _{CC} =-30V, I _C =-150mA,I _{B1} =I _{B2} =-15mA

h_{FE} Classification And Marking

Print Mark 2T

Classification

 h_{FE} 100~300